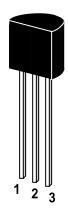
NPN Silicon Epitaxial Planar Transistor

For low-frequency power amplification and driver Amplification. Complementary to 2SA683 to and 2SA684.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

		Symbol	Value	Unit
Collector Base Voltage 2SC	1383	V_{CBO}	30	V
2SC	1384	V_{CBO}	60	V
Collector Emitter Voltage 2SC	1383	V_{CEO}	25	V
2SC	1384	V_{CEO}	50	V
Emitter Base Voltage		V_{EBO}	5	V
Peak Collector Current		I _{CP}	1.5	А
Collector Current		I _C	1	А
Power Dissipation		P _{tot}	1	W
Junction Temperature		T_j	150	$^{\circ}\!\mathbb{C}$
Storage Temperature Range		Ts	-55 to +150	$^{\circ}\!\mathbb{C}$







ST 2SC1383 / 2SC1384

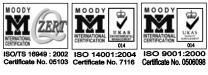
Characteristics at T_{amb}=25 °C

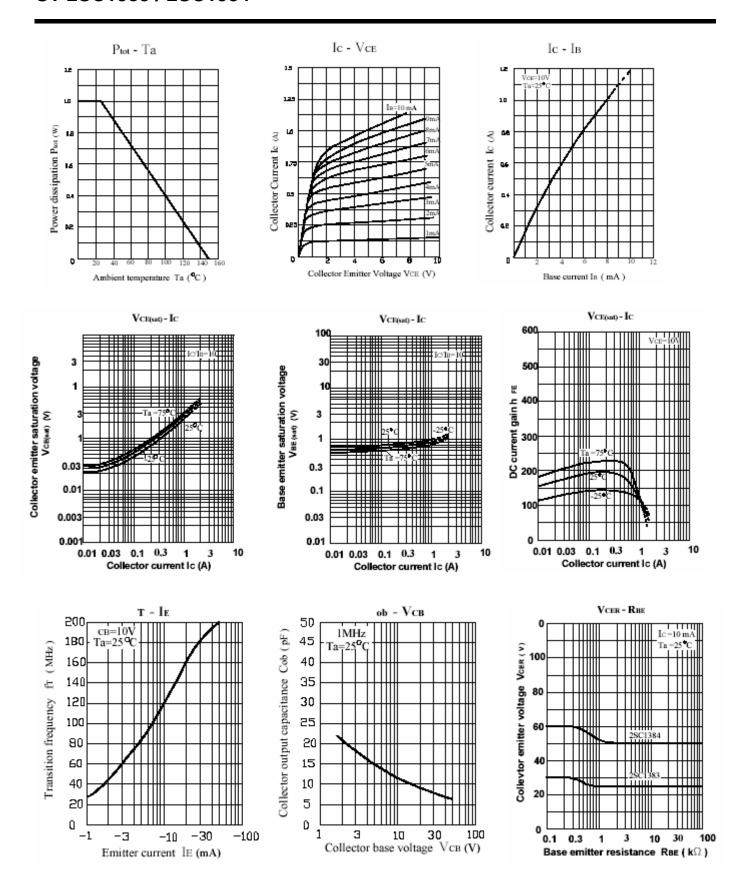
			Symbol	Min.	Тур.	Max.	Unit
DC Current Gain							
at I _C =500mA, V _{CE} =10V							
		Q	h _{FE}	85	-	170	-
		R	h _{FE}	120	-	240	-
		S	h _{FE}	170	-	340	-
at I _C =1A, V _{CE} =5V			h _{FE}	50	100	-	-
Collector Cutoff Current							
at V _{CB} =20V			I _{CBO}	-	-	0.1	μΑ
Collector Base Voltage							
at I _C =10μA	2SC1383		V_{CBO}	30	-	-	V
	2SC1384		V_{CBO}	60	-	-	V
Collector Emitter Voltage							
at I _C =2mA	2SC1383		V_{CEO}	25	-	-	V
I _C =2mA	2SC1384		V_{CEO}	50	-	-	V
Emitter Base Voltage							
at I _E =10μA			V_{EBO}	5	-	-	V
Collector Saturation Voltage							
at I_C =500mA, I_B =50mA			V _{CE(sat)}	-	0.2	0.4	V
Base Saturation Voltage							
at I _C =500mA, I _B =50mA			V _{BE (sat)}	-	0.85	1.2	V
Gain Bandwidth Product		_					
at V_{CB} =10V, I_E =-50mA, f =200MHz		f _T		200	-	MHz	
Output Capacitance							
at V _{CB} =10V,f=1MHz			СОВ		11	20	pF













SEMTECH ELECTRONICS LTD.

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